

The Silicon Vertex Detector of the Belle II Experiment

Klemens Lautenbach For the Belle II SVD Collaboration International Conference on High Energy Physics – ICHEP2022, Bologna

Outline

- SuperKEKB, Belle II and the Silicon Vertex Detector
- Operation and Performance
- Beam Background
- Radiation Damage Effects
- Summary

SuperKEKB



- Belle II is hosted at the SuperKEKB accelerator
 - Asymmetric energy e+e- (4 & 7 GeV) collider in Tsukuba, Japan
 - Nominal CMS energy 10.58 GeV = M(Y(4S)), Y(5S) and Y(6S) also producible
- Full event reconstruction, decays with neutral/soft particles
- Goal for SuperKEKB: 50x integrated Belle luminosity → 50/ab
 - nano-beam-scheme : ~6 x 10³⁵ cm⁻² s⁻¹
 - 30x KEKB instantaneous luminosity
- So far ~420/fb are collected since March 2019
 - 4.7 x 10³⁴ cm⁻² s⁻¹ instantaneous luminosity in June 2022

Belle II

- Vertex Detector VXD
 - Composed of PXD (2 layers) and SVD (4 layers)
- **Pixeldetector PXD**
 - DEPFET pixel sensor, layers 1 & 2
 - Innermost layer 14 mm from interaction point
- Silicon Vertex Detector SVD
 - Double-sided silicon strip sensors (DSSD), layers 3,4,5,6
 - Innermost layer at 40 mm
- SVD requirements from precision physics program:
 - Good vertex resolution
 - Improved point resolution, reduced inner • radius, low material budget
 - Extrapolate tracks to PXD
 - Used to define Region of Interest (ROI) for • data reduction
 - ROI calculated by CPU farm (HLT) •
 - Stand-alone tracking for low p^T tracks
 - PID with dE/dx
 - Precise K_s vertexing



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lautenbach@cppm.in2p3.fr

Silicon Vertex Detector (SVD) - I

• SVD concept: DSSDs

- 2D positioning information
- Strips are AC-coupled to n-type substrate
- Fully depleted at 20-60 V, operated at 100 V



AC-coupled strips on N-type substrate Full depletion voltage: 20-60V Operation voltage: 100V



- SVD layout
 - 3 different DSSD shapes
 - 172 sensors, 224k readout strips
 1.2 m² total sensor area



*readout strips - one floating strip on both sides

Silicon Vertex Detector (SVD) - II

- Low material budget: 0.7% X₀ per layer
- Signal connected to front-end ASICs by flex circuits
 - Layer 3 chips outside the active area
 - chip-on-sensor for layer 4, 5 and 6



- Diamond sensors for radiation monitor and beam abort
 - Operation in high background environment, hit rates of 3 MHz/cm² at R = 40 mm
 - Radiation hardness at nominal luminosity: 0.2 Mrad/yr at R = 40 mm

physics acceptance: $\theta = 17-150^{\circ}$



SVD front-end ASICS – APV25

- Originally developed for CMS silicon tracker
 - Fast: 50 ns shaping times
 - Radiation hard: > 100 Mrad
 - Power consumption: 0.4 W/chip (700 W in total)
 - 128 channel inputs per chip
- Operated in "multi-peak" mode
 @ ~32 MHz clock
 - Bunch-crossing frequency ~8*32 MHz, clock not synchronous with them as in CMS
 - 6 subsequent samples read-out





Origami chip on sensor concept

- Readout chips directly on each middle sensor:
 - shorter signal propagation length (smaller capacitance and noise)
 - Thinned to 100 μm to reduce material budget
- Wrapped flex to read both sides from the same side
- Cool only one side with two-phase CO2 (-20° C) cooling







Operation Experience

- Reliable and smooth operation with no major issues since installation
 - Total fraction of masked strips < 1%
 - One APV25 chip (out of 1748) disabled in spring 2019, fixed by cable reconnection in summer 2019
 - Temperature and calibration constants are evolving gradually
- Excellent detector performance
 - Average sensor hit efficiency > 99% and stable with time
 - Updated simulation better agrees with data
 - Reasonable cluster charge distribution



→ Continuous data taking during anti-COVID measures, thanks to an excellent shifter/operator/coordinator team (local and remote)

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Signal charge and signal to noise ratio

Signal charge depends on the incident angle and varies $d = 320 - 300 \mu m$ with sensor position [Backward (BWD), Forward (FWD)] d cosi Normalized for the track path length in silicon (E*d/l) similar in all sensors and consistent with expectations 20 avers [cm] sensor Very good cluster Signal to Noise Ratio (SNR) in all 172 sensors (most probable value: 13-30) 10 Normalized for path length (320 µm) BWD FWD 0.25 z [cm] Belle II - SVD 4 u/P side Entries / 2ke--30 -20 -10 0 10 20 30 L3.x.2 sensors v/N side 0.3 Entries / 50 bins 0.2 Belle II - SVD Data: exp. 10 run 5834 +u/P side Candidate hadronic events L3.x.2 sensors V/N side 0.25 Data: exp. 10 run 5834 MPV for MIP 0.15 Candidate hadronic events signal, 24 ke 0.2 $SNR = \frac{\sum S_i}{\sum N_i^2}$ 0.1 0.15 0.05 0.1 0.05 20 80 100 60 120 40 Cluster Charge (ke-) u/P side: charge in agreement v/N side: 10%-30% signal loss with expectation from MIP taking 20 80 100 due to large pitch and presence into account 15% uncertainty in Cluster SNR of floating strips APV25 gain calibration u/P side: larger noise due to longer strip length (larger inter-strip capacitance)

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Cluster position resolution



- Excellent resolution on the position is crucial for good quality reconstructed tracks and vertices
- Resolution estimated from residual of the cluster position w.r.t unbiased track extrapolation using $e^+e^- \rightarrow \mu^+\mu^-$ events
- Effect of track extrapolation error is subtracted
- Good resolution, generally in agreement with pitch expectations
 - Black dashed and dotted line in lower right plot



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-40 - 35 - 30 - 25 - 20 - 15 - 10 - 5

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Hit-time resolution

- Excellent hit time resolution (< 3 ns) w.r.t. event time provided by Central Drift Chamber (event t₀)
- Able to efficiently reject off-time background hits
 - Will be used for higher luminosity and background levels
 - A tighter selection can be achieved by removing the trigger jitter contribution (hit time $-t_0$)
- Improvement in High Level Trigger performance by using SVD hit time to compute the event t0:
 → same resolution and 2000 times faster computation time w.r.t. the CDC event t0.



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Beam background and hit occupancy limit

- Beam background increases SVD hit occupancy \rightarrow tracking performance suffers
- Current occupancy limit in layer 3 is ~3%
 → hit time cut could increase this number to 5%, due to improved background rejection
 - Studies with SVD standalone tracking ongoing to validate the performance (benchmark finding efficiency > 90% and fake rate < 20%)
 - Average hit occupancy in layer 3 is around 0.5% and well under control at current luminosity
 - At a benchmark luminosity of L = 8 x 10³⁵ cm⁻² s⁻¹, we expect an average occupancy of about 3% in layer-3 (estimated scaling MC with data/MC ratio)**



** Large uncertainties on long term background extrapolation, computed assuming optimal collimator settings and without injection background **

Small safety factor and large uncertainties on expected beam background motivate the vertex detector upgrade

→ improve tolerance to hit rates and radiation; technology assessment ongoing

More in the upgrade talk by Peter Krizan



Integrated dose

• Estimated by using the good correlation measured on data among SVD occupancy and diamond dose



Integrated dose in SVD Layers

- SVD dose in the last 2022 period
 ~ 20 krad in most exposed layer 3 mid
 plane sensors
 - Total SVD integrated dose on layer 3 mid plane < 70 krad
 - 1-MeV equivalent neutron fluence evaluated to be ~1.6 x 10^{11} neq/cm² in first 3 years (assume neq/dose fluence ratio = 2.3 x 10^9 neq/cm²/krad from simulation)

Radiation effect: leakage current



- Good linear correlation between leakage current and estimated dose as expected from NIEL model $\Delta I = \alpha \phi_{eq} V$ assuming a constant dose / ϕ_{eq} ratio
- Slope of the same order of magnitude as BaBar measurement* (1 μm/cm²/Mrad at 20° C)
 - preliminary results show large variations due to temperature effects and dose spread among sensors in layer (average dose in layer used in estimate)
- Irradiation is not expected to degrade SVD performance, even up to 6 Mrad:
 - SNR expected to be still > 10
 - leakage current will contribute to strip noise increase
 - Currently, noise increase dominated by sensor interstrip capacitance due to the short APV25 shaping time

*[NIMA 729, 615-701, 2013]

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Radiation effect: strip noise vs. dose

- Noise increase is ~10-30% not affecting performance
- Induced by radiation effects on sensor surface: non-linear increase due to fixed oxide charges in irradiated sensors that increase inter-strip capacitance
 - already saturated on n-side and layer 3 p-side, still rising on outer layer p-side
 - leakage current increase has no effect on strip noise due to short APV shaping time



Radiation effect: bulk damage effect

- Bulk damage can change effective doping and depletion voltage
- Measure depletion voltage with scan (n-side strip noise vs. bias voltage)
 - n-side strips insulated only when the n-type bulk is fully depleted → minimum strip noise full depletion
 - Over-depletion bias still slightly decrease noise



Summary

- SVD has been taking data smoothly in Belle II since March 2019
 - reliable operation and excellent stable performance!
- Observed first effects of radiation damage, not affecting performance
- System prepared to cope with higher background by rejecting off-time background, exploiting the excellent SVD hit time resolution

SVD technical paper accepted by JINST, available on arXiv: https://arxiv.org/abs/2201.09824



Thank You!



Luminosity projection of SuperKEKB



Target scenario: extrapolation from 2021 run including expected improvements.

Base scenario: conservative extrapolation of SuperKEKB parameters from 2021 run.

- We start long shutdown I (LSI) from summer 2022 for 15 months to replace VXD. There will be other maintenance/improvement works of machine and detector.
- We resume physics running from Fall 2023.
- A SuperKEKB International Taskforce (aiming to conclude in summer 2022) is discussing additional improvements.
- An LS2 for machine improvements could happen on the time frame of 2026-2027

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